Dual 4-input multiplexer; 3-state Rev. 1 — 17 July 2012

Product data sheet

1. **General description**

The 74HC253-Q100; 74HCT253-Q100 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC253-Q100; 74HCT253-Q100 provides a dual 4-input multiplexer with 3-state outputs which selects 2 bits of data from up to four sources selected by common data select inputs (S0, S1). The two 4-input multiplexer circuits have individual active LOW output enable inputs $(1\overline{OE}, 2\overline{OE})$.

The 74HC253-Q100 and 74HCT253-Q100 are the logic implementation of a 2-pole, 4-position switch, where the position of the switch is determined by the logic levels applied to S0 and S1. The outputs are forced to a high-impedance OFF-state when nOE is HIGH.

The logic equations for the outputs are:

$$1Y = 1\overline{OE} \bullet (110 \bullet \overline{S1} \bullet \overline{S0} + 111 \bullet \overline{S1} \bullet S0 + 112 \bullet S1 \bullet \overline{S0} + 113 \bullet S1 \bullet S0)$$

 $2Y = 2\overline{OE} \bullet (2I0 \bullet \overline{S1} \bullet \overline{S0} + 2I1 \bullet \overline{S1} \bullet S0 + 2I2 \bullet S1 \bullet \overline{S0} + 2I3 \bullet S1 \bullet S0)$

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

Features and benefits 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Non-inverting data path
- 3-state outputs interface directly with system bus
- Complies with JEDEC standard no. 7A
- Common select inputs
- Separate output enable inputs
- Input levels:
 - For 74HC253-Q100: CMOS level
 - For 74HCT253-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)



Dual 4-input multiplexer; 3-state

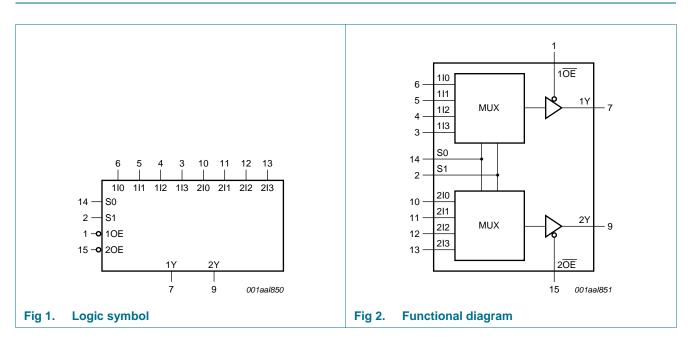
3. Applications

- Data selectors
- Data multiplexers

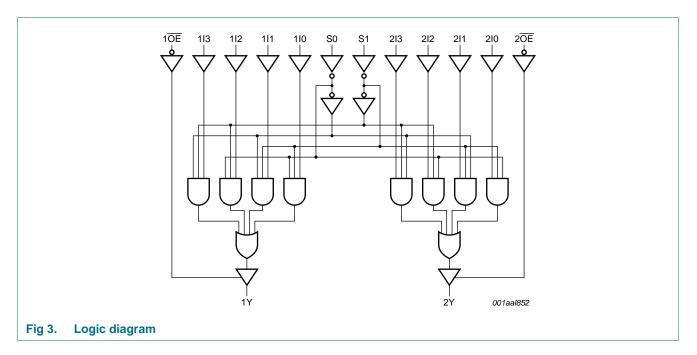
4. Ordering information

Table 1. Ordering information										
Type number Package										
	Temperature range	Name	Description	Version						
74HC253D-Q100	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width	SOT109-1						
74HCT253D-Q100			3.9 mm							

5. Functional diagram

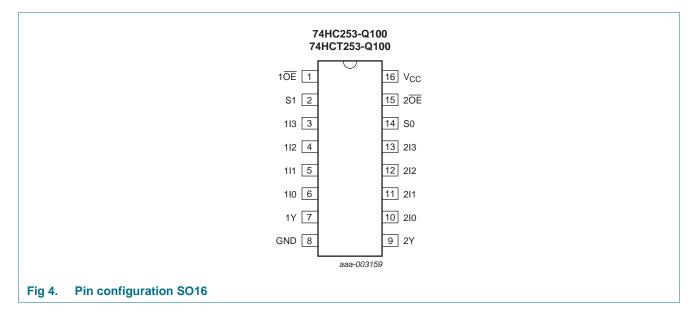


Dual 4-input multiplexer; 3-state



6. Pinning information

6.1 Pinning



Dual 4-input multiplexer; 3-state

6.2 Pin description

Table 2. Pin des	cription	
Symbol	Pin	Description
1 <u>0E</u> , 2 <u>0E</u>	1, 15	output enable inputs (active LOW)
S0, S1	14, 2	data select inputs
110, 111, 112, 113	6, 5, 4, 3	data inputs source 1
1Y	7	multiplexer output source 1
GND	8	ground (0 V)
2Y	9	multiplexer output source 2
210, 211, 212, 213	10, 11, 12, 13	data inputs source 2
V _{CC}	16	supply voltage

7. Functional description

Table 3.Function table^[1]

select In	puts	data inp	uts			output enable	output
S0	S1	nl0	nl1	nl2	nl3	nOE	nY
х	Х	Х	Х	Х	Х	Н	Z
L	L	L	Х	Х	Х	L	L
L	L	Н	Х	Х	Х	L	Н
Н	L	Х	L	Х	Х	L	L
Н	L	Х	Н	Х	Х	L	Н
L	Н	Х	Х	L	Х	L	L
L	Н	Х	Х	Н	Х	L	Н
Н	Н	Х	Х	Х	L	L	L
Н	Н	Х	Х	Х	Н	L	Н

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±50	mA
I _O	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±35	mA
I _{CC}	supply current		-	70	mA
I _{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		-65	+150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T_{amb} = -40 °C to +125 °C			
		SO16 package	[2] _	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC2	53-Q100		74HCT	253-Q10	0	Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC25	3-Q100									
V _{IH}		$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	L LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 6.0 \ \text{V}$	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -6.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -7.8 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V

Dual 4-input multiplexer; 3-state

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Un
			Min	Тур	Max	Min	Max	Min	Max	
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_0 = 20 \ \mu A; V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 6.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current		-	-	±0.5	-	±5.0	-	±10.0	μA
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	-	80	-	160	μA
Cı	input capacitance		-	3.5	-					pF
74HCT2	53-Q100									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
0	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = -6 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	V_{I} = V_{IH} or $V_{IL};V_{CC}$ = 4.5 V								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA}$	-	0.15	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	$V_{I} = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_{O} = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_{O} = 0$ A	-	-	±0.5	-	±5.0	-	±10	μΑ
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	8.0	-	80	-	160	μA
∆l _{CC}	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 2.1 \text{ V};\\ \text{other inputs at } V_{CC} \text{ or GND};\\ V_{CC} = 4.5 \text{ V to 5.5 V};\\ I_{O} = 0 \text{ A} \end{array}$								
		per input pin; 1In, 2In inputs	-	40	144	-	180	-	196	μA
		per input pin; nOE input	-	110	396	-	495	-	539	μA
		per input pin; Sn input	-	110	396	-	495	-	539	μA
Cı	input capacitance		-	3.5	-					pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

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Dual 4-input multiplexer; 3-state

11. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); For test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions		25	°C	–40 °C to +85 °C	–40 °C to +125 °C	Unit
				Тур	Max	Max	Max	
74HC253	3-Q100							
pd	propagation delay	1In to 1Y or 2In to 2Y; see <u>Figure 5</u>	<u>[1]</u>					
		$V_{CC} = 2.0 V$		55	175	220	265	ns
		$V_{CC} = 4.5 V$		20	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		17	-	-	-	ns
		$V_{CC} = 6.0 V$		16	30	37	45	ns
		Sn to nY; see Figure 5						
		$V_{CC} = 2.0 V$		58	175	220	265	ns
		$V_{CC} = 4.5 V$		21	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		18	-	-	-	ns
		$V_{CC} = 6.0 V$		17	30	37	45	ns
en	enable time	nOE to nY; see Figure 6	[2]					
		$V_{CC} = 2.0 V$		30	100	125	150	ns
		$V_{CC} = 4.5 V$		11	20	25	30	ns
		$V_{CC} = 6.0 V$		9	17	21	26	ns
t _{dis} disable time	disable time	nOE to nY; see Figure 6	[3]					
		$V_{CC} = 2.0 V$		41	150	190	225	ns
		$V_{CC} = 4.5 V$		15	30	38	45	ns
		$V_{CC} = 6.0 V$		12	26	33	38	ns
·t	transition time	see Figure 5	[4]					
		$V_{CC} = 2.0 V$		14	60	75	90	ns
		$V_{CC} = 4.5 V$		5	12	15	18	ns
		$V_{CC} = 6.0 V$		4	10	13	15	ns
C _{PD}	power dissipation capacitance	per multiplexer; $V_1 = GND$ to V_{CC}	<u>[5]</u>	55	-			pF
74HCT2	53-Q100							
t _{pd}	propagation delay	1In to 1Y or 2In to 2Y; see <u>Figure 5</u>	<u>[1]</u>					
		$V_{CC} = 4.5 V$		20	38	48	57	ns
		V_{CC} = 5.0 V; C _L = 15 pF		17	-	-		ns
		Sn to nY; see Figure 5						
		V _{CC} = 4.5 V		22	40	50	60	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		19	-			ns
t _{en}	enable time	$n\overline{OE}$ to nY; V _{CC} = 4.5 V; see <u>Figure 6</u>	[2]	14	30	38	45	ns

Dual 4-input multiplexer; 3-state

Symbol	Parameter	Conditions		25	25 °C –40 °C to +85 °C		–40 °C to +125 °C	Unit
				Тур	Max	Max	Max	
t _{dis}	disable time	$n\overline{OE}$ to nY; V _{CC} = 4.5 V; see <u>Figure 6</u>	<u>[3]</u>	13	30	38	45	ns
t _t	transition time	V_{CC} = 4.5 V; see <u>Figure 5</u>		5	12	15	18	ns
C _{PD}	power dissipation capacitance	per multiplexer; $V_I = GND$ to V_{CC}	<u>[5]</u>	55	-			pF

Table 7. Dynamic characteristics ... continued

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 $[1] \quad t_{pd} \text{ is the same as } t_{PHL}, \, t_{PLH}.$

[2] t_{en} is the same as t_{PZH} , t_{PZL} .

[3] t_{dis} is the same as t_{PHZ} , t_{PLZ} .

- [4] t_t is the same as t_{THL} , t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 P_{D} = $C_{PD} \times V_{CC}{}^{2} \times f_{i} \times N$ + $\Sigma (C_{L} \times V_{CC}{}^{2} \times f_{o})$ where:

 f_i = input frequency in MHz;

fo = output frequency in MHz;

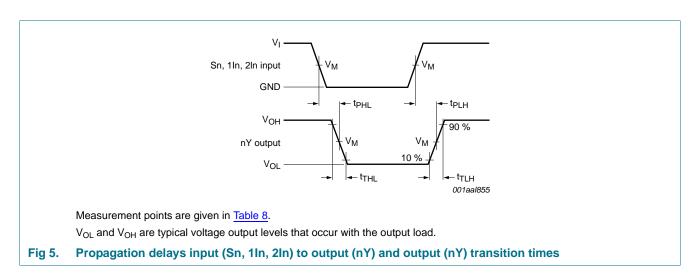
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of outputs.

12. Waveforms



Dual 4-input multiplexer; 3-state

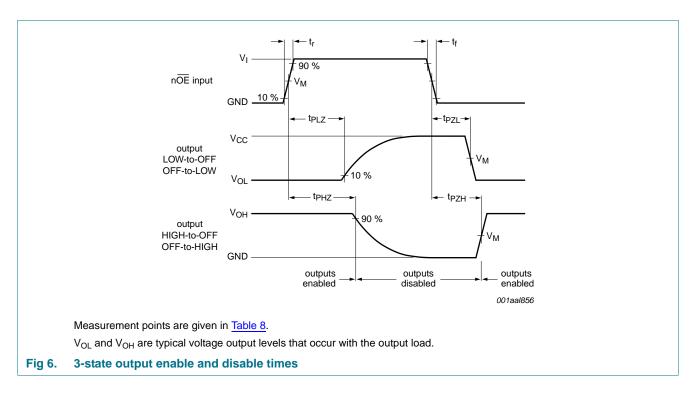


Table 8.Measurement points

Туре	Input	Output
	V _M	V _M
74HC253-Q100	0.5V _{CC}	0.5V _{CC}
74HCT253-Q100	1.3 V	1.3 V

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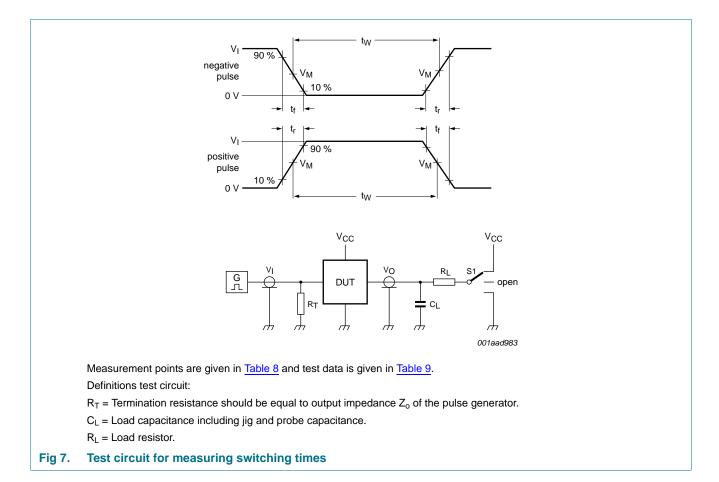


Table 9. Test data

Туре	Input		Load		Switch position		
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
74HC253-Q100	V _{CC}	6 ns	50 pF	1 kΩ	open	GND	V _{CC}
74HCT253-Q100	3 V	6 ns	50 pF	1 kΩ	open	GND	V _{CC}

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13. Package outline

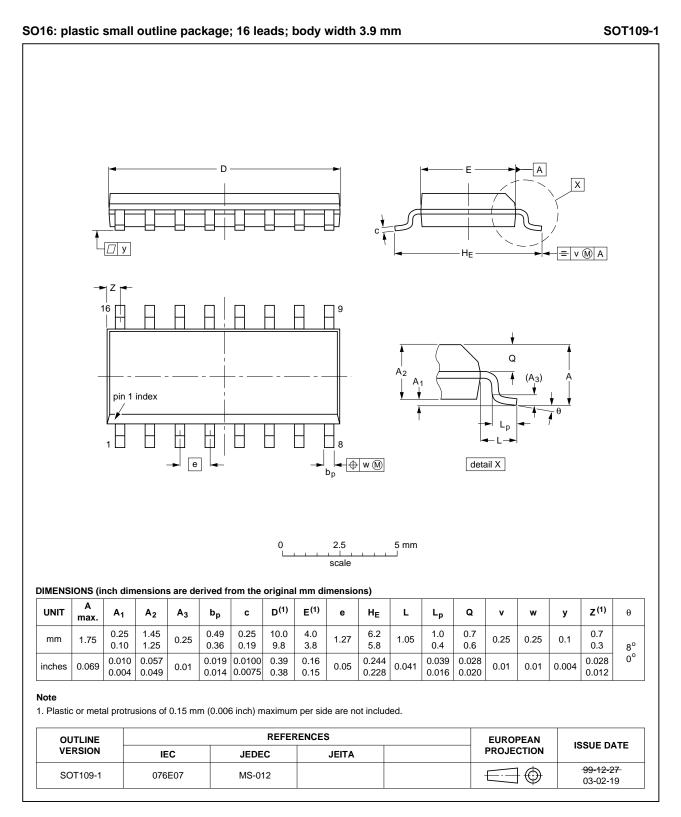


Fig 8. Package outline SOT109-1 (SO16)

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74HC_HCT253_Q100

Dual 4-input multiplexer; 3-state

14. Abbreviations

Description
Complementary Metal Oxide Semiconductor
Device Under Test
ElectroStatic Discharge
Human Body Model
Machine Model
Transistor-Transistor Logic
Military

15. Revision history

Table 11. Revision history	1. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74HC_HCT253_Q100 v.1	20120717	Product data sheet	-	-	

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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18. Contents

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